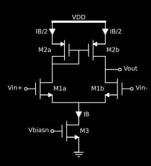
Use gm/ID methodology to design a diff input SE output operational transconductance amplifier (OTA) that achieves the following specs. Use an ideal external 10uA DC current source in your test bench (not included in the OTA current consumption spec), but design your own current mirror.

Spec.	
Technology	65nm CMOS
Supply Voltage	1.2 V
Open loop DC voltage gain	≥ 34 dB
CMRR @ DC	≥ 74 dB
Phase Margin	≥ 70°
OTA Current Consumption	≤ 20 uA
Reference current	10 uA
CM input range low	$\leq 0.6  \mathrm{V}$
CM input range high	≥ 1 V
GBW	≥ 5 MHz

## Design steps

- Av not too high So, achieved by single stage
- CMIR Spec is 0.8 V < CMIR < 1.5 V Closer to the VDD rail, , I used NMOS input stage. The implemented architecture is shown in figure below.



$$\text{GBW} = \frac{g_{\text{m1}}}{2\pi C_{\text{L}}} \geq 5 \text{ MHz} \rightarrow g_{\text{m1}} \geq 157.1 \text{ uS}$$

$$g_{m1} = 175 \text{ uS} \rightarrow \text{:: } I_{SS} = 2*I_{D1} \rightarrow I_{D1} = 10 \text{ uA}$$

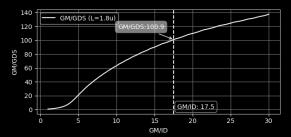
$$\therefore \frac{g_{m1}}{I_D} = \frac{175}{10} = 17.5$$

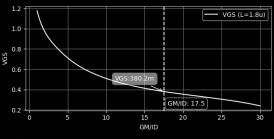
$$A_{V} = 50 = g_{m1} (r_{o1} \parallel r_{o2})$$

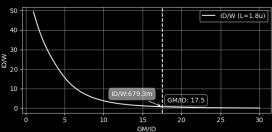
Assume 
$$r_{o1}=r_{o2}=r_o \rightarrow A_V=g_{m1}\frac{r_o}{2}$$

Assume 
$$V_{DS1} = V_{DS2} = 400 \text{ mV} \rightarrow V_{SB1} = 400 \text{ mV}$$

$$: 100 = g_{m1} r_o \rightarrow L_1 = 1.8u$$







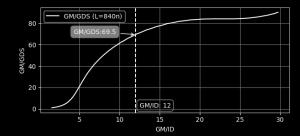
$$V_{GS1} = 380.2 \text{ mV}$$

$$\frac{I_D}{W_1} = 679.3 \text{ m} \rightarrow W_1 = 14.75 \text{ um}$$

Assume 
$$\frac{g_{m2}}{I_D} = 12 \rightarrow g_{m2} = 120 \text{ uS}$$

$$\because A_V = g_{m1} \frac{r_o}{2} = 50 \rightarrow r_o = 571.5 \text{ k}\Omega$$

$$\therefore g_{m2} r_{o2} = 68.6$$

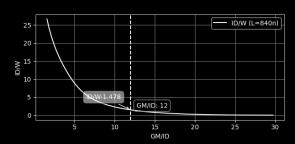


$$\because \mathsf{CMIR}_{\mathsf{H}} \geq 1 \rightarrow \ \because \mathsf{V}_{\mathsf{GS1}} - \mathsf{V}_1^* - \mathsf{V}_{\mathsf{SG2}} + \mathsf{V}_{\mathsf{DD}} \geq 1$$

$$V_{SG2} \leq 466 \text{ mV} \rightarrow \div \frac{g_{m,2}}{I_D} | min = 9.8 \frac{S}{A}$$

Choose same  $\frac{g_{m2}}{I_D} = 12$  as my asumption

$$L_2=840~\text{nm} \rightarrow V_{GS2}=419.8~\text{m}$$



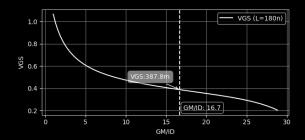
$$\frac{I_D}{W_2} = 1.478 \rightarrow W_2 = 6.76 \text{ um}$$

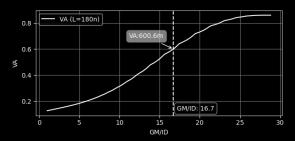
$$\therefore A_{V,CM} = \frac{-1}{2 g_{m,2} R_{SS}} = 34 - 74 = -40 \text{ dB}$$

$$\therefore \, R_{SS} \geq 417 \; k\Omega \rightarrow r_{o3} \geq 417 \; k\Omega$$

$$Assume\ L_{CM} = 3*L_{min} = 180\ nm$$

Assume 
$$V_{DS,CM} = V^* = 120 \text{ mV} \rightarrow \frac{g_{mCM}}{I_D} = 16.7$$



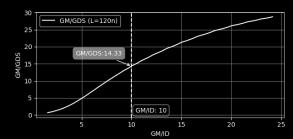


$$\label{eq:VGS,CM} \div \text{V}_{\text{GS,CM}} = 387.8 \text{ m} \rightarrow \div \text{V}_{\text{A}} = 600.6 \text{ mV}$$

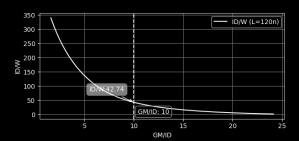
$$r_{\text{oCM}} = 30 \; k\Omega \rightarrow R_{\text{out}} = (g_m \; r_o)_{\text{CASC}} \, r_{\text{oCM}} = 420 \; k$$

$$(g_m r_o)_{CASC} = 14$$

bias it in SI 
$$\left(\frac{g_m}{I_D}\right)_{CASC} = 10 \rightarrow \text{for large } r_o$$



$$\therefore L_{CASC} = 120 \text{ nm} \rightarrow V_{GS,CASC} = 520.7 \text{m}$$



$$\because \frac{I_D}{W_{CASC}} = 42.74 \rightarrow \therefore W_{CASC} = 470 \text{ nm}$$

$$: I_{Ref} * R_{CM} = VGS_{CASC} + V^* - VGS_{CM}$$

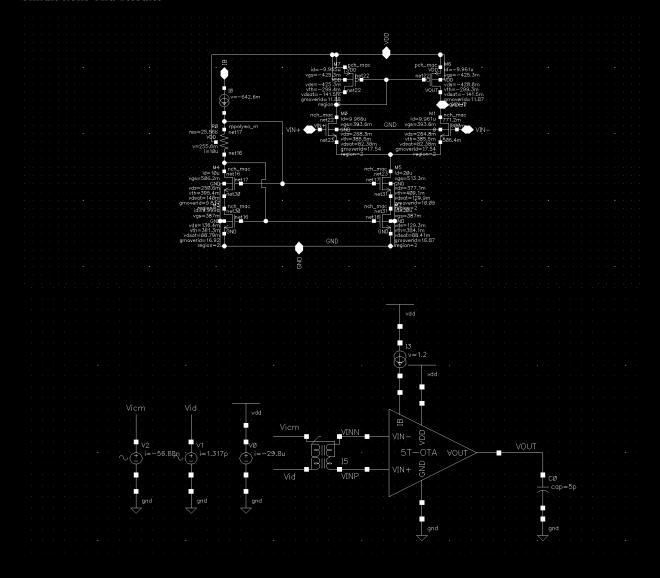
$$R_{\text{CM}} = \frac{520.7m + 120m - 387.8m}{10~\text{u}} = 25.3~\text{k}\Omega$$

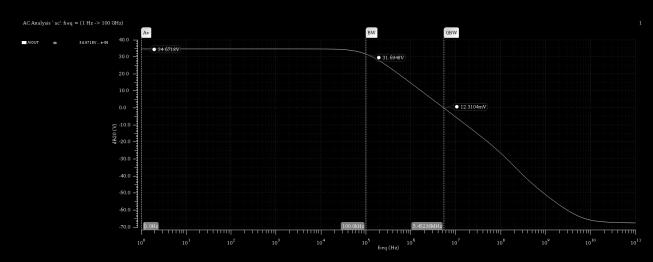
$$\because \mathsf{CMIR}_{\mathsf{L}} \leq 0.8 \rightarrow \therefore \mathsf{V}_{\mathsf{GS1}} + V_{\mathit{DsatCASC}} + \mathsf{V}_{\mathsf{CM}}^* \leq 0.6$$

$$V_{CASC}^* \leq 100 \; mV \rightarrow \frac{g_{m,CASC}}{I_D} | min = 10 \; S/A$$

L1	1.8u	W1	14.75u
L2	840n	W2	6.76u
LCASC	120n	WCASC	470n
LCM	180n	WCM	2.8u

## Simulations and Results





AC Analysis act freq =  $(1 \text{ Hz} \cdot > 100 \text{ GHz})$ 

